Claims

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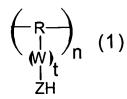
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- 1. A process for imaging a photoresist comprising the steps of,
 - a) forming a coating of a photoresist on a substrate;
- b) forming a barrier coating over the photoresist from a barrier coating solution;
- c) imagewise exposing the photoresist and the barrier coating using immersion lithography, further where the immersion lithography comprises an immersion liquid between the barrier coating and exposure equipment; and
 - d) developing the coatings with an aqueous alkaline solution.
- 2. The process of claim 1, where the barrier coating is insoluble in the immersion liquid.

3. The process of claim 1, where the immersion liquid comprises water.

- 4. The process of claim 1, where the barrier coating is soluble in an aqueous alkaline solution.
- 5. The process of claim 1, where exposure is with radiation between 150 nm and 450nm.
- 6. The process of claim 1, where exposure is with radiation between 150 nm and 300 nm.
 - 7. The process of claim 1, where the photoresist is sensitive to exposure wavelength between 150 nm and 450 nm.
- 30 8. The process of claim 1, where the barrier coating comprises an alkyl alcohol solvent and a polymer comprising an ionizable group.
 - 9. The process of claim 8, where the polymer comprising the ionizable group has a pKa ranging from about -9 to about 11.

10. The process of claim 8, where the polymer has the structure



- where, R is a polymeric backbone, W is a spacer group, ZH is the ionizable group, and t=0-5.
 - 11. The process of claim 8, where R is selected from a multicyclic polymeric backbone, a monocyclic backbone, a linear aliphatic backbone, a branched aliphatic backbone, an aromatic backbone, a fluorinated alkyl backbone, and mixtures thereof.

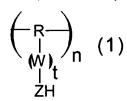
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- 12. The composition of claim 8, where ZH is selected from -C(C_nF_{2n+1})₂OH (n=1-8), -PhOH, (SO₂)₂ NH, (SO₂)₃CH, (CO)₂NH, SO₃H, PO₃H and CO₂H.
- 13. The composition of claim 8, where the polymer is poly(3-(bicyclo[2.2.1]hept-5-en-2-yl)-1,1,1-trifluoro-2-(trifluoromethyl)propan-2-ol).
- 14. The process of claim 8, where the solvent is selected from an alkyl alcohol with the structure HOC_nH_{2n+1} , where n is between 3 and 12.
 - 15. The process of claim 8, where the solvent further comprises an n-alkane solvent with the structure C_nH_{2n+2} , where n is between 3 and 12.
- 16. The process of claim 1, where the aqueous alkaline solution comprises tetramethyl ammonium hydroxide.
 - 17. A barrier coating solution for a photoresist imaged with immersion lithography, where the barrier coating comprises an alkyl alcohol solvent and a polymer comprising an ionizable group, further where pKa of the ionizable group ranges from about -9 to about 11.

18. The composition of claim 17, where the polymer has the structure



- where, R is the polymeric backbone, W is a spacer group, ZH is the ionizable group, and t=0-5.
- 19. The composition of claim 18, where R is selected from a multicyclic polymeric backbone, a monocyclic backbone, a linear aliphatic backbone, a
 10 branched aliphatic backbone, an aromatic backbone, a fluorinated alkyl backbone and mixtures thereof.
 - 20. The composition of claim 18, where ZH is selected from -C(C_nF_{2n+1})₂OH (n=1-8), -PhOH, (SO₂)₂ NH, (SO₂)₃CH, (CO)₂NH, SO₃H, PO₃H and CO₂H.

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- 21. The composition of claim 18, where the polymer is poly(3-(bicyclo[2.2.1]hept-5-en-2-yl)-1,1,1-trifluoro-2-(trifluoromethyl)propan-2-ol).
- 22. The composition of claim 17, where the solvent is selected from an alkyl alcohol with the structure HOC_nH_{2n+1}, where n is between 3 and 7.
 - 23. The composition of claim 17, where the solvent further comprises an n-alkane solvent with the structure C_nH_{2n+2} , where n is between 3 and 7.